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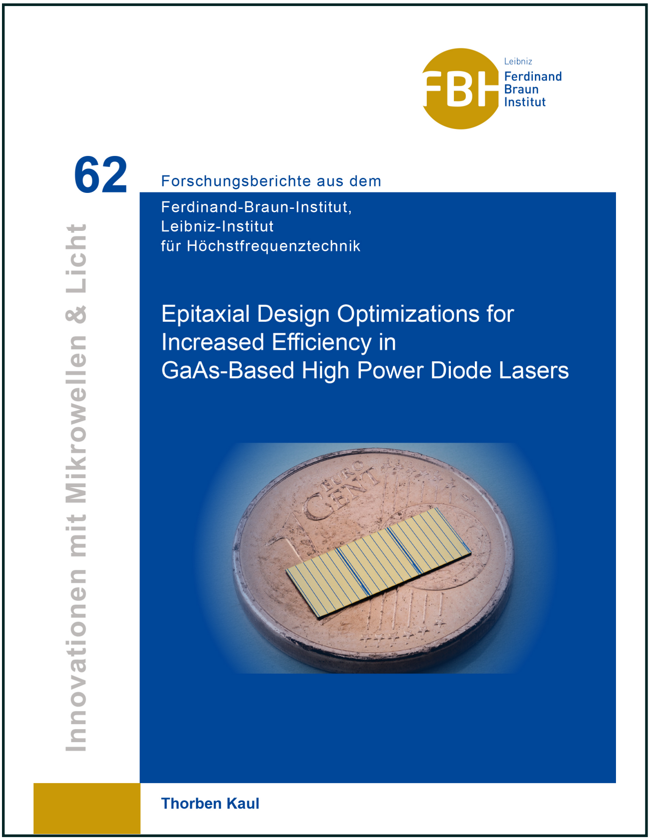
# Epitaxial Design Optimizations for Increased Efficiency in GaAs-Based High Power Diode Lasers

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